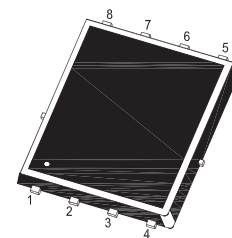
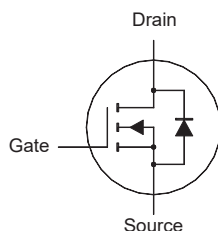


N-Channel Enhancement Mode MOSFET
Features

- Surface-mounted package
- Low Gate-Source Threshold Voltage
- Halogen and Antimony Free(HAF), RoHS compliant

Application

- Load switch
- PWM applications
- LCD TV CCFL inverter



1.Source 2.Source 3.Source 4.Gate
5.Drain 6.Drain 7.Drain 8.Drain
DFN5060 Plastic Package

Key Parameters

Parameter	Value	Unit
BV _{DSS}	65	V
R _{DS(ON)} Max	11 @ V _{GS} = 10 V	mΩ
	16.5 @ V _{GS} = 4.5 V	
V _{GS(th)} typ	1.7	V
Q _g typ	15 @ V _{GS} = 10 V	nC

Absolute Maximum Ratings(at T_a = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	65	V
Gate-Source Voltage	V _{GS}	± 20	V
Drain Current	I _D	45	A
		28	
	T _c = 25°C T _c = 100°C		
Peak Drain Current, Pulsed ¹⁾	I _{DM}	160	A
Avalanche Current	I _{AS}	12	A
Single Pulse Avalanche Energy ²⁾	E _{AS}	36	mJ
Power Dissipation	P _D	31.2	W
	T _c = 25°C		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to + 150	°C

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	R _{θJC}	4	°C/W
Thermal Resistance from Junction to Ambient ³⁾	R _{θJA}	50	°C/W

¹⁾ Pulse Test: Pulse Width ≤ 100 μs, Duty Cycle ≤ 2%, Repetitive rating, pulse width limited by junction temperature T_{J(MAX)} = 150°C.

²⁾ Limited by T_{J(MAX)}, starting T_J = 25 °C, L = 0.5 mH, R_g = 25 Ω, I_{AS} = 12 A, V_{GS} = 10 V.

³⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 250\ \mu\text{A}$	BV_{DSS}	65	-	-	V
Drain-Source Leakage Current at $V_{DS} = 52\ \text{V}$	I_{DSS}	-	-	1	μA
Gate Leakage Current at $V_{GS} = \pm 16\ \text{V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	$V_{GS(th)}$	1.2	-	2.5	V
Drain-Source On-State Resistance at $V_{GS} = 10\ \text{V}$, $I_D = 10\ \text{A}$ at $V_{GS} = 4.5\ \text{V}$, $I_D = 8\ \text{A}$	$R_{DS(on)}$	- -	8.1 -	11 16.5	m Ω
DYNAMIC PARAMETERS					
Forward Transconductance at $V_{DS} = 5\ \text{V}$, $I_D = 5\ \text{A}$	g_{fs}	-	14	-	S
Gate Resistance at $V_{GS} = 0\ \text{V}$, $V_{DS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	R_g	-	1.3	-	Ω
Input Capacitance at $V_{GS} = 0\ \text{V}$, $V_{DS} = 30\ \text{V}$, $f = 1\ \text{MHz}$	C_{iss}	-	830	-	pF
Output Capacitance at $V_{GS} = 0\ \text{V}$, $V_{DS} = 30\ \text{V}$, $f = 1\ \text{MHz}$	C_{oss}	-	260	-	pF
Reverse Transfer Capacitance at $V_{GS} = 0\ \text{V}$, $V_{DS} = 30\ \text{V}$, $f = 1\ \text{MHz}$	C_{rss}	-	20	-	pF
Gate charge total at $V_{DS} = 30\ \text{V}$, $I_D = 10\ \text{A}$, $V_{GS} = 10\ \text{V}$ at $V_{DS} = 30\ \text{V}$, $I_D = 10\ \text{A}$, $V_{GS} = 4.5\ \text{V}$	Q_g	- -	15 7	- -	nC
Gate to Source Charge at $V_{DS} = 30\ \text{V}$, $I_D = 10\ \text{A}$, $V_{GS} = 10\ \text{V}$	Q_{gs}	-	3	-	nC
Gate to Drain Charge at $V_{DS} = 30\ \text{V}$, $I_D = 10\ \text{A}$, $V_{GS} = 10\ \text{V}$	Q_{gd}	-	3	-	nC
Turn-On Delay Time at $V_{DD} = 30\ \text{V}$, $I_D = 10\ \text{A}$, $V_{GS} = 10\ \text{V}$, $R_g = 4.7\ \Omega$	$t_{d(on)}$	-	10	-	ns
Turn-On Rise Time at $V_{DD} = 30\ \text{V}$, $I_D = 10\ \text{A}$, $V_{GS} = 10\ \text{V}$, $R_g = 4.7\ \Omega$	t_r	-	16	-	ns
Turn-Off Delay Time at $V_{DD} = 30\ \text{V}$, $I_D = 10\ \text{A}$, $V_{GS} = 10\ \text{V}$, $R_g = 4.7\ \Omega$	$t_{d(off)}$	-	9	-	ns
Turn-Off Fall Time at $V_{DD} = 30\ \text{V}$, $I_D = 10\ \text{A}$, $V_{GS} = 10\ \text{V}$, $R_g = 4.7\ \Omega$	t_f	-	2	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $I_S = 1\ \text{A}$, $V_{GS} = 0\ \text{V}$	V_{SD}	-	-	1.2	V
Body-Diode Continuous Current	I_S	-	-	45	A
Body-Diode Continuous Current, Pulsed	I_{SM}	-	-	160	A
Body Diode Reverse Recovery Time at $I_S = 10\ \text{A}$, $di/dt = 100\ \text{A} / \mu\text{s}$	t_{rr}	-	17	-	ns
Body Diode Reverse Recovery Charge at $I_S = 10\ \text{A}$, $di/dt = 100\ \text{A} / \mu\text{s}$	Q_{rr}	-	7	-	nC

Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

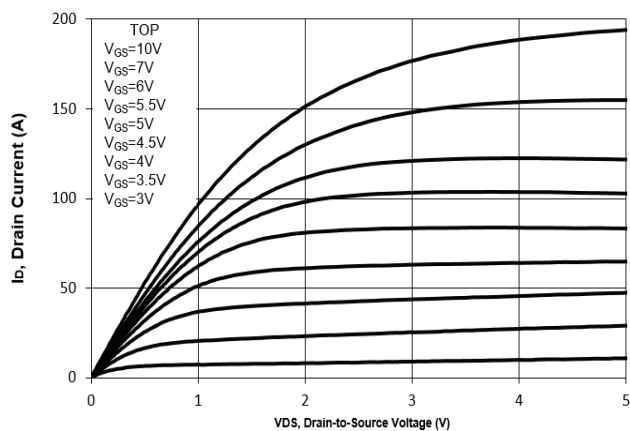


Fig. 2 Typical Transfer Characteristics

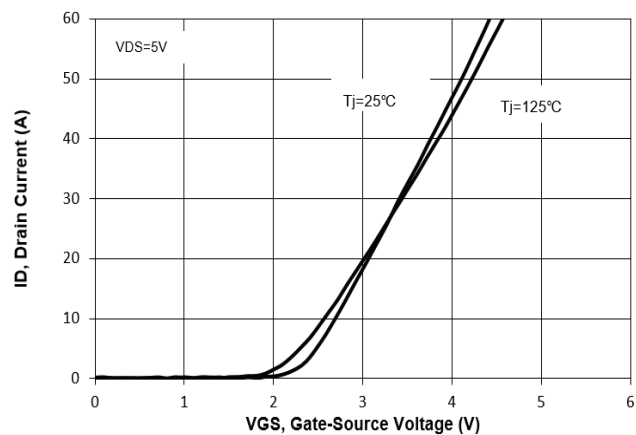


Fig. 3 on-Resistance vs. Drain Current

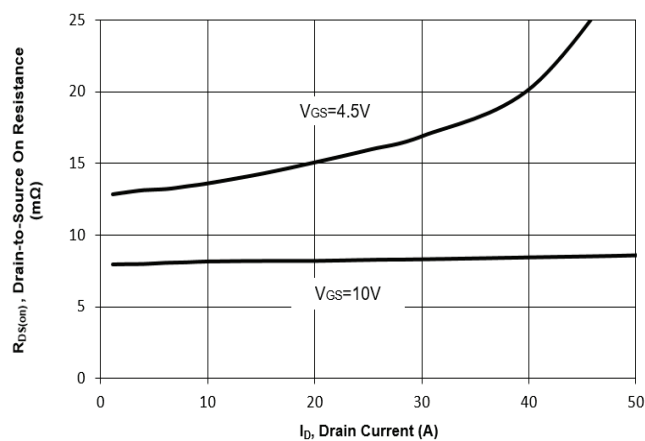


Fig. 4 on-Resistance vs. Gate to Source Voltage

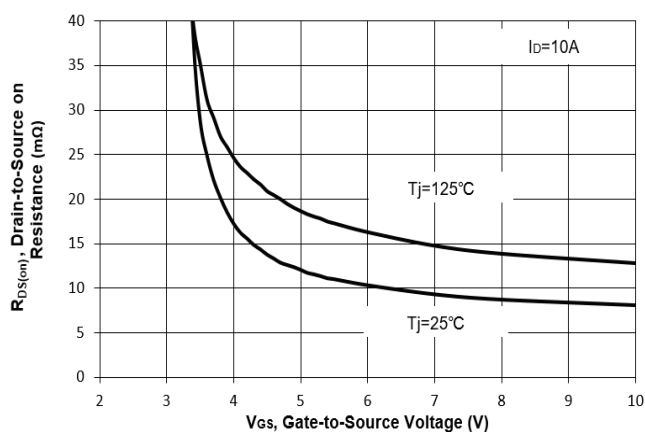


Fig. 5 on-Resistance vs. T_J

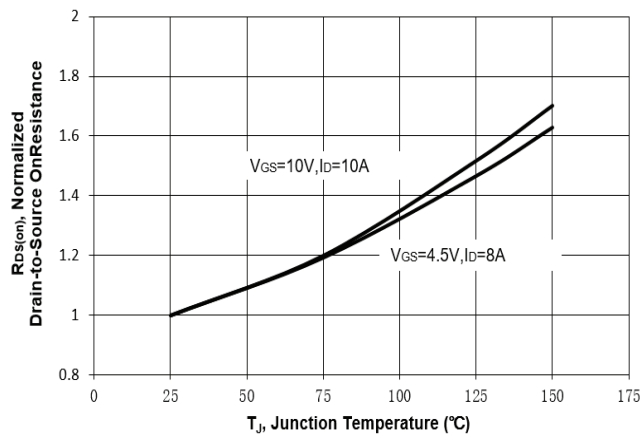
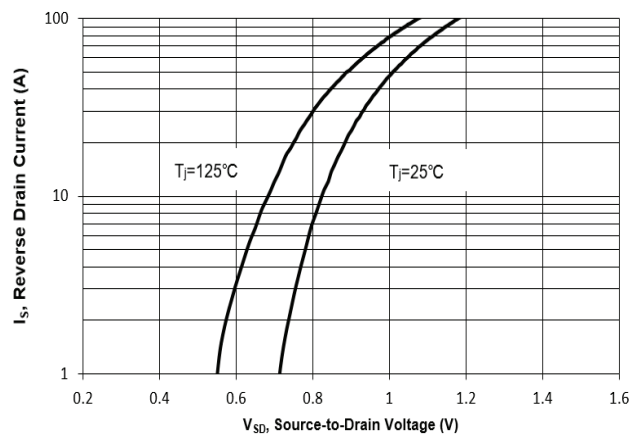


Fig. 6 Typical Body Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 13 Normalized Maximum Transient Thermal Impedance($Z_{\theta JC}$)

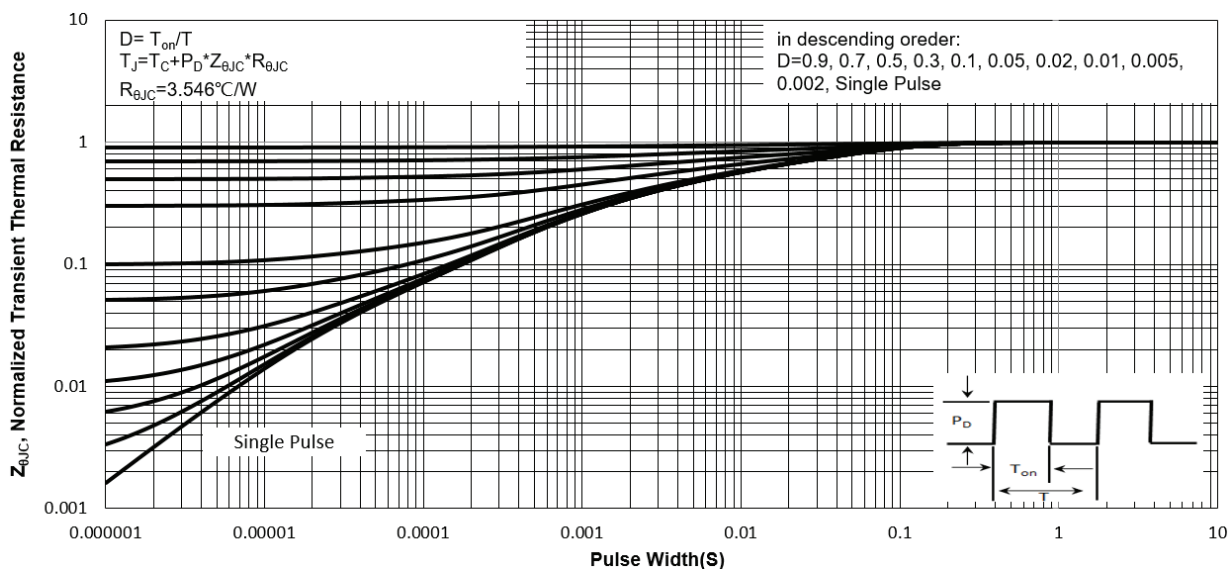
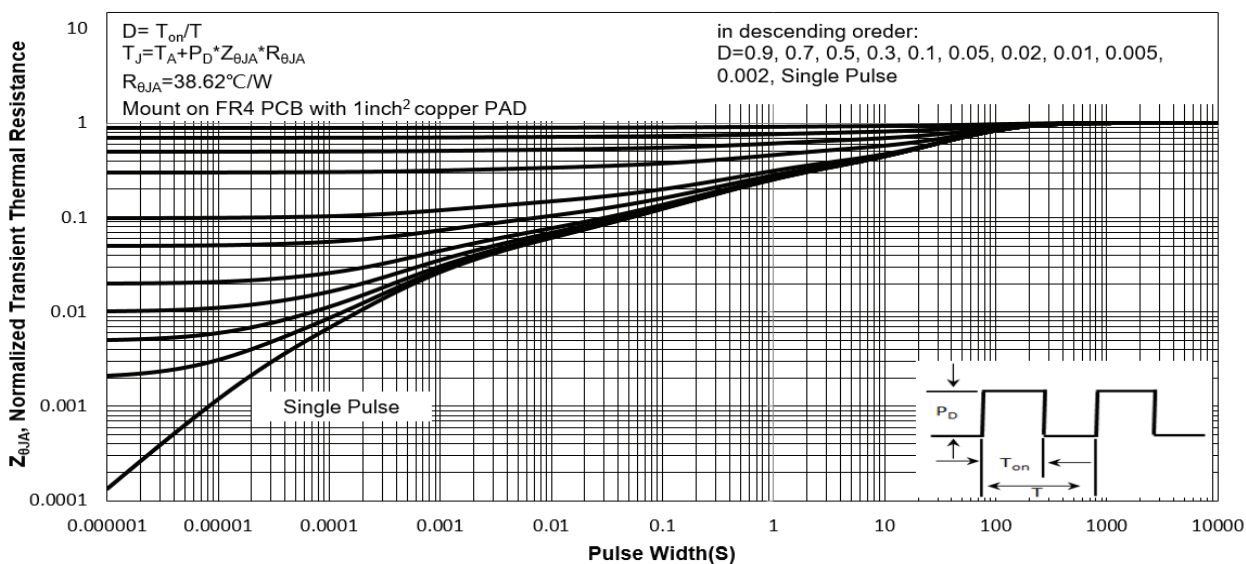
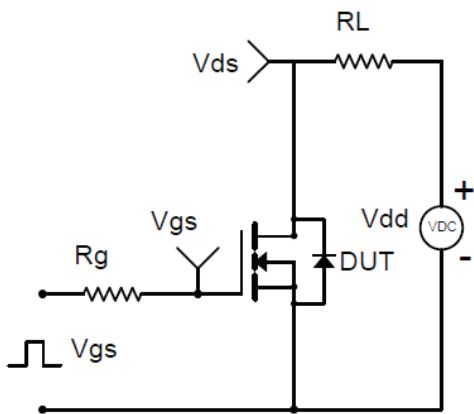
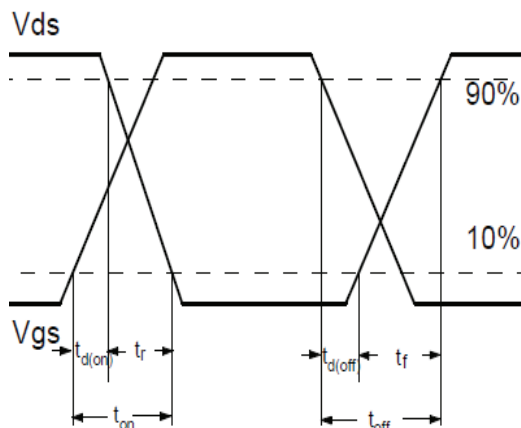
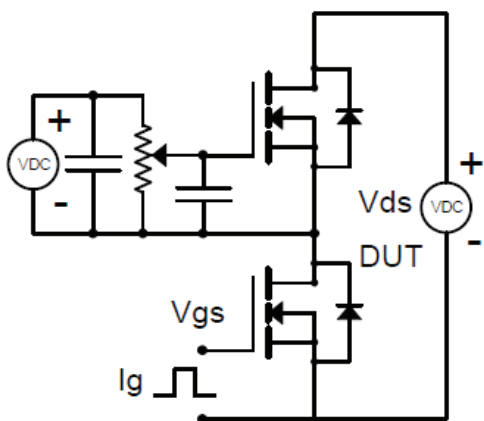
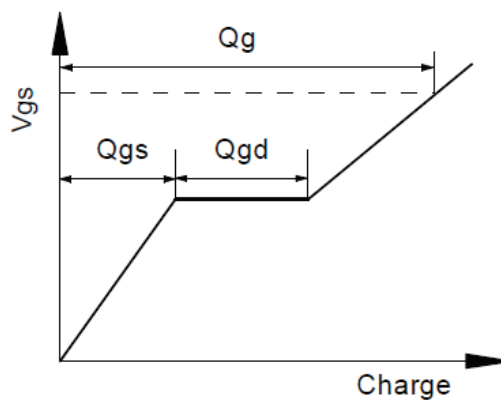
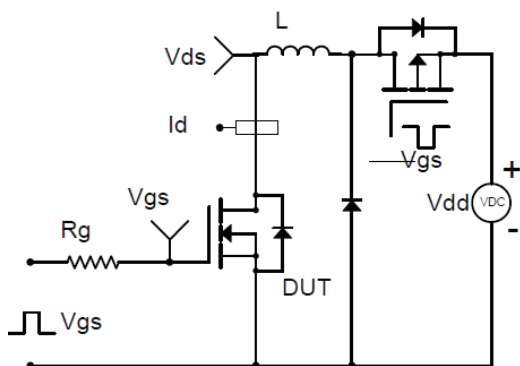
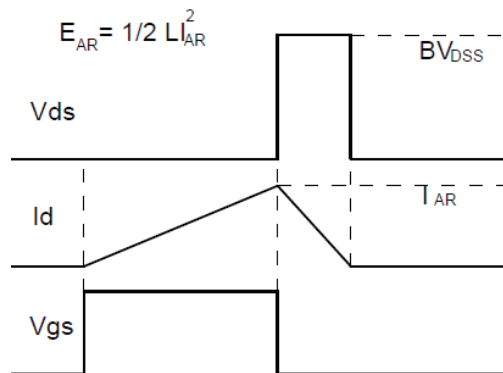


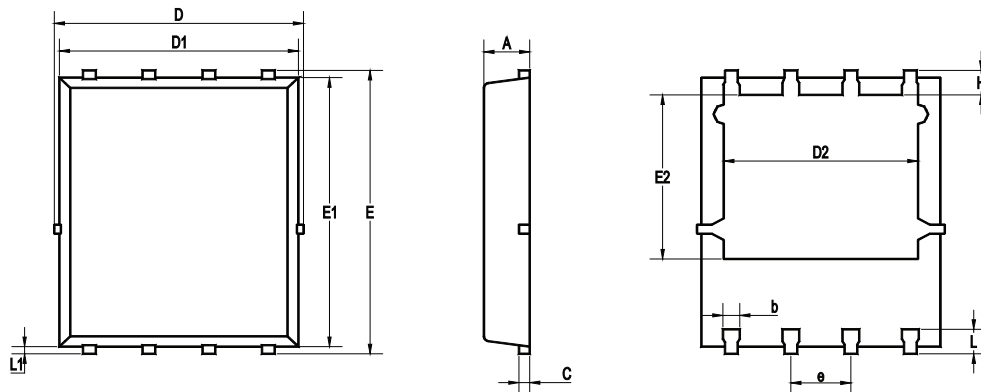
Fig. 14 Normalized Maximum Transient Thermal Impedance($Z_{\theta JA}$)



Test Circuits
Fig.1-1 Switching times test circuit

Fig.1-2 Switching Waveform

Fig.2-1 Gate charge test circuit

Fig.2-2 Gate charge waveform

Fig.3-1 Avalanche test circuit

Fig.3-2 Avalanche waveform


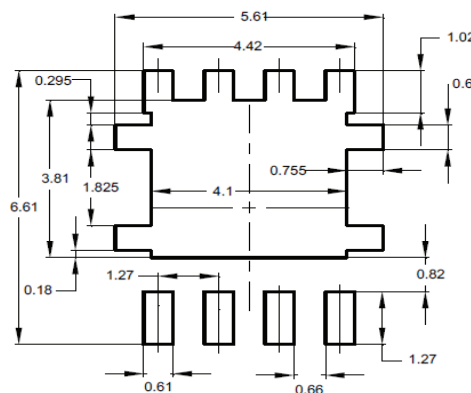
Package Outline Dimensions (Units: mm)

DFN5060



UNIT	A	b	C	D	D1	D2	E	E1	E2	e	L	L1	H
mm	1.12 0.9	0.51 0.33	0.34 0.11	5.26 4.7	5.1 4.7	4.5 3.56	6.25 5.75	6 5.6	3.66 3.18	1.37 1.17	0.71 0.35	0.2 0.06	0.71 0.35

Recommended Soldering Footprint



Packing information

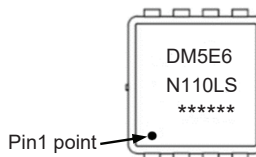
Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN5060	12	8 ± 0.1	0.315 ± 0.004	330	13	5,000

Marking information

" DM5E6N110LS " = Part No.

" ***** " = Date Code Marking

Font type: Arial



Disclaimer: Our company reserve the right to make modifications, enhancements, improvements, corrections or other changes to improve product design, functions and reliability, anytime without notice.

Fig. 7 Typical Junction Capacitance

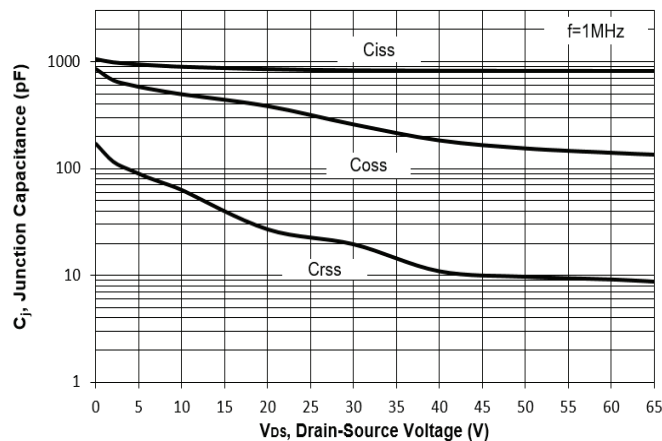


Fig. 8 Drain-Source Leakage Current vs. T_j

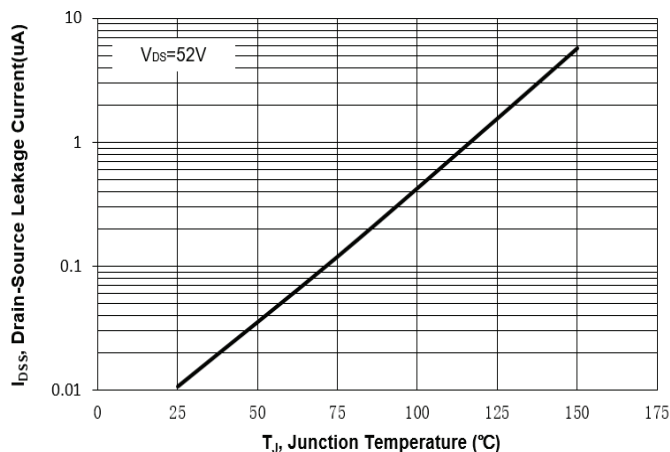


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

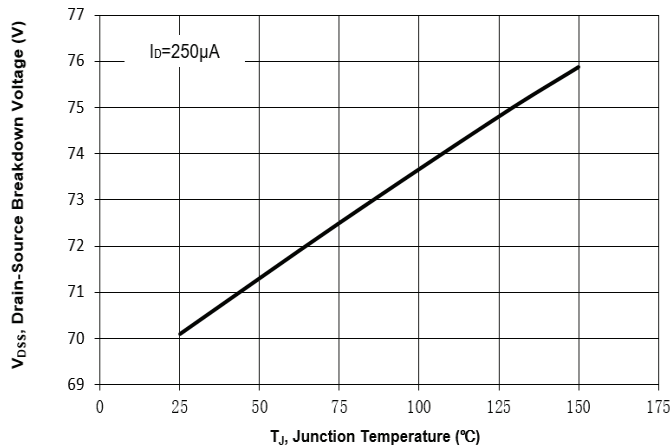


Fig. 10 Gate Threshold Variation vs. T_j

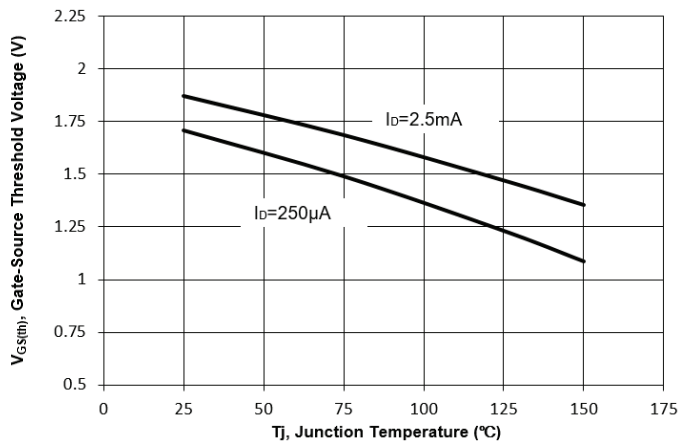


Fig. 11 Gate Charge

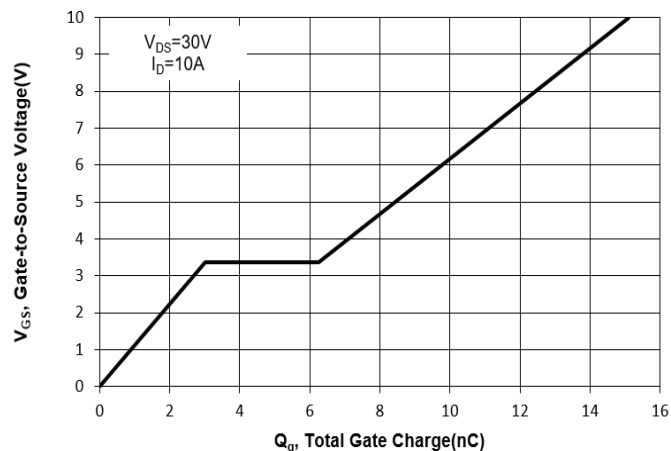


Fig. 12 Safe Operation Area

